

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

1. A device $[(100, 200, 300)]$ for depositing a layer $[(20)]$ based on polycrystalline silicon onto a substantially plane, elongate, moving support $[(4)]$ having two longitudinal faces $[(43, 44)]$ and two longitudinal side edges $[(41, 42)]$, the device comprising:

· a crucible $[(1)]$ containing a bath $[(2)]$ of molten silicon, said support $[(4)]$ being designed to be dipped at least in part in the bath and to pass substantially vertically in its long direction through the equilibrium surface $[(21)]$ of the bath; and

· at least one edge control element $[(5, 5', 15, 15')]$, each edge control element being maintained substantially vertically close to one of the two longitudinal side edges $[(41, 42)]$;

each edge control element comprising walls $[(51 \text{ to } 53', 151 \text{ to } 153')]$ defining a longitudinal slot $[(54, 54', 154, 154')]$ beside the corresponding longitudinal side edge, each slot being dipped in part in the bath $[(2)]$ so as to raise the level of the bath by capillarity in the vicinity of the corresponding longitudinal side edge,

~~the device being characterized in that~~ wherein at least one of the walls $[(51 \text{ to } 52', 151 \text{ to } 152')]$, referred to as an "insertion" wall, facing part of one of the longitudinal faces, is substantially plane.

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2. A device ~~[(100, 200, 300)]~~ according to claim 1, for depositing a layer based on polycrystalline silicon and comprising two edge control elements, in which each edge control element includes two substantially plane insertion walls.

3. A device ~~[(100, 200, 300)]~~ according to claim 2, for depositing a layer based on polycrystalline silicon, the device being ~~characterized in that~~ wherein the insertion walls are either parallel ~~[(51 to 52', 151 to 152')]~~ or else outwardly flared.

4. A device ~~[(100, 200, 300)]~~ according to claim 2 ~~[(or claim 3)]~~, for depositing a layer based on polycrystalline silicon, ~~the device being characterized in that~~ wherein the mean depth of each slot ~~[(54, 154')]~~ is less than 1 cm.

5. A device ~~[(100, 200, 300)]~~ according to ~~[[any one of]]~~ clam~~[[s]]~~ 2 ~~[[to 4]]~~, for depositing a layer based on polycrystalline silicon, ~~the device being characterized in that~~ wherein the mean spacing between the insertion walls ~~[(51 to 52', 151 to 152')]~~ is less than 7 mm.

6. A device ~~[(100, 200)]~~ according to ~~[[any one of]]~~ claim~~[[s]]~~ 2 ~~[[to 5]]~~, for depositing a layer based on polycrystalline silicon, ~~the device being characterized in that~~ wherein the crucible ~~[(1) comprises]]~~ has a bottom ~~[(11)]~~ and side walls ~~[(12)]~~, and each of the edge control elements ~~[(5, 5')]~~ being stationary and held vertically by the bottom.

7. A device ~~[(100, 200)]~~ according to ~~[[any one of]]~~ claim~~[[s]]~~ 2 ~~[[to 5]]~~, for depositing

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a layer based on polycrystalline silicon, ~~the device being characterized in that~~ wherein the crucible ~~[[comprises]]~~ has a bottom ~~[[((11))]]~~ and side walls ~~[[((12))]]~~, and each of the edge control elements ~~[[((5, 5'))]]~~ extend longitudinally to the bottom and preferably forms a monolithic structure with the bottom.

8. A device ~~[[((100, 200))]]~~ according to claim 7, for depositing a layer based on polycrystalline silicon, ~~the device being characterized in that~~ wherein each of the edge control elements ~~[[((5, 5'))]]~~ presents at least one orifice ~~[[((7, 7'))]]~~ dipped in the bath ~~[[((2))]]~~ and suitable for feeding silicon to said element, the orifice being preferably of millimeter order and situated close to the bottom.

9. A device (300) according to any one of claims 2 to 6, for depositing a layer based on polycrystalline silicon, the device being characterized in that each of the edge control elements (15, 15') comprises a plate including said slot (154, 154'), the plate being brought into contact with the equilibrium surface (21) of the bath.

10. A device ~~[[((300))]]~~ according to claim 9, for depositing a layer based on polycrystalline silicon, ~~the device being characterized in that~~ wherein contact with the surface ~~[[((21))]]~~ of the bath takes place by means of a connection ~~[[((17, 17'))]]~~ between the plate and displacement means ~~[[((19, 19'))]]~~ external to the crucible ~~[[((1))]]~~, and preferably allowing vertical displacement only.

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11. A device [(300)] according to claim 9 [or claim 10], for depositing a layer based on polycrystalline silicon, ~~the device being characterized in that~~ wherein each plate [(15, 15') comprises]] has a disk including said slot [(154, 154')] and presenting an effective diameter greater than 10 mm, and preferably equal to about 12 mm.

12. A device [(300)] according to [[any one of]] claim[[s]] 9 [[to 11]], for depositing a layer based on polycrystalline silicon, ~~the device being characterized in that~~ wherein the mean spacing between the insertion walls [(151 to 152')] is about 2 mm.

13. A device [(100, 200, 300)] according [[any one of]] claim[[s]] 1 [[to 12]], for depositing a layer based on polycrystalline silicon, ~~the device being characterized in that~~ wherein each of the edge control elements [(5, 5', 15, 15')] is made of a material that does not react with silicon and that is preferably selected from graphite, silicon carbide, and silicon nitride.

14. A device [(100, 200, 300)] according [[any one of]] claim[[s]] 1 [[to 13]], for depositing a layer based on polycrystalline silicon, ~~the device being characterized in that~~ wherein each of the edge control elements [(5, 5', 15, 15')] is made of a material presenting emissivity greater than the emissivity of silicon.